

**isc Silicon NPN RF Transistor**
**BFR540**
**DESCRIPTION**

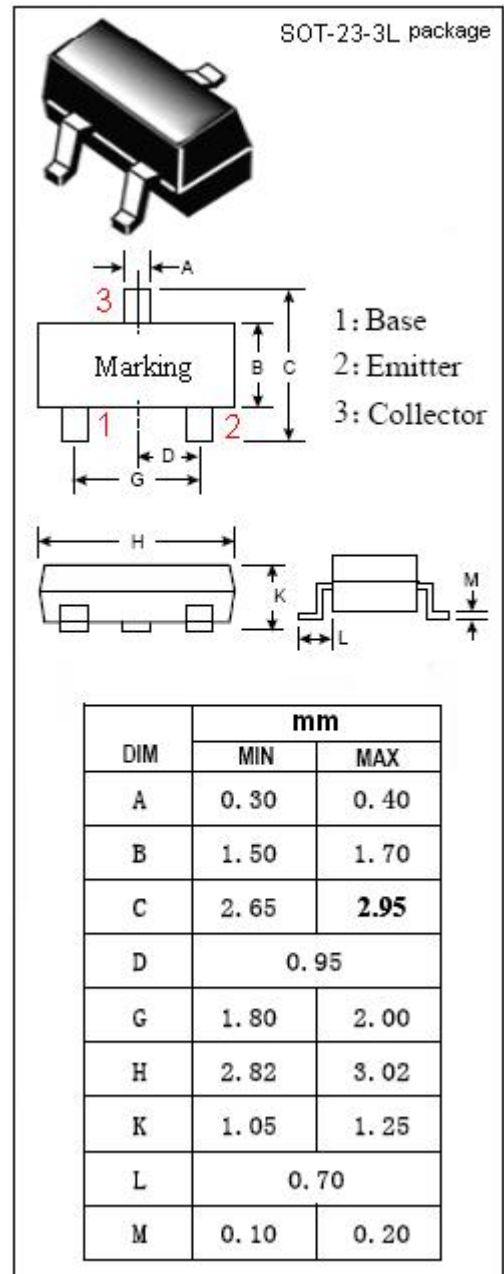
- High Power Gain
- High Current Gain Bandwidth Product
- Low Noise Figure
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for RF frontend in wideband applications in the GHz range, such as analog and digital cellular telephones, cordless telephones (CT1, CT2, DEC, etc.).

**ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	20	V
V <sub>CES</sub>	Collector-Emitter Voltage	15	V
V <sub>EBO</sub>	Emitter-Base Voltage	2.5	V
I <sub>c</sub>	Collector Current-Continuous	120	mA
P <sub>c</sub>	Collector Power Dissipation @T <sub>c</sub> =25°C	0.5	W
T <sub>J</sub>	Junction Temperature	175	°C
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C



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**ELECTRICAL CHARACTERISTICS**

 T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I <sub>CB0</sub>	Collector Cutoff Current	V <sub>CB</sub> = 8V; I <sub>E</sub> = 0			50	nA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 40mA; V <sub>CE</sub> = 8V	100		250	
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 40mA; V <sub>CE</sub> = 8V; f= 1GHz		9		GHz
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 8V; f= 1MHz		0.9		pF
C <sub>re</sub>	Feedback Frequency	I <sub>E</sub> = 0; V <sub>CB</sub> = 8V; f= 1MHz		0.6		pF
PG	Power Gain	I <sub>C</sub> = 40mA; V <sub>CE</sub> = 8V; f= 900MHz		14		dB
PG	Power Gain	I <sub>C</sub> = 40mA; V <sub>CE</sub> = 8V; f= 2GHz		7		dB
S <sub>21e</sub>   <sup>2</sup>	Insertion Power Gain	I <sub>C</sub> = 40mA; V <sub>CE</sub> = 8V; f= 900MHz	12	13		dB
NF	Noise Figure	I <sub>C</sub> = 10mA; V <sub>CE</sub> = 8V; f= 900MHz		1.3	1.8	dB
NF	Noise Figure	I <sub>C</sub> = 40mA; V <sub>CE</sub> = 8V; f= 900MHz		1.9	2.4	dB
NF	Noise Figure	I <sub>C</sub> = 10mA; V <sub>CE</sub> = 8V; f= 2GHz		2.1		dB
V <sub>o</sub>	Output Voltage	I <sub>C</sub> = 40 mA; V <sub>CE</sub> = 8 V; Z <sub>L</sub> = Z <sub>S</sub> = 75 Ω		550		mV

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